

SEMITOP® 3

IGBT Module

SK10GD12T4ET

Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor

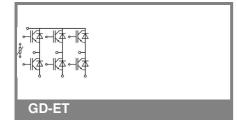
Typical Applications*

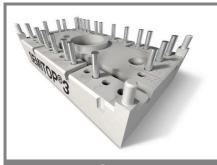
Remarks

• $V_{CE,sat}$, V_F = chip level value

Absolute Maximum Ratings $T_s = 25 ^{\circ}\text{C}$, unless otherwise specified					
Symbol IGBT	Conditions			Values	Units
V _{CES}	T _j = 25 °C			1200	V
I _C	T _j = 175 °C	$T_s = 25 ^{\circ}\text{C}$ $T_s = 70 ^{\circ}\text{C}$		17 15	A A
I _{CRM}	I _{CRM} = 3 x I _{Cnom}	1 _s - 70 0		24	A
V_{GES}				± 20	V
t _{psc}	V_{CC} = 800 V; $V_{GE} \le 15$ V; VCES < 1200 V	T _j = 150 °C		10	μs
Inverse Diode					
I _F	T _j = 175 °C	T_s = 25 °C		15	Α
		$T_s = 70 ^{\circ}C$		12	Α
I _{FRM}	I _{FRM} = 3 x I _{Fnom}			24	Α
Module					
I _{t(RMS)}					Α
T _{vj}				-40 + 175	°C
T _{stg}				-40 +12 5	°C
V _{isol}	AC, 1 min.			2500	V

Characteristics $T_s =$		25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0.3 \text{ mA}$		5	5,8	6,5	V
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = V_{CES}$	T _j = 25 °C			1,0	mA
		T _j = 150 °C				mA
I_{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C			120	nA
		T _j = 150 °C				nA
V _{CE0}		T _j = 25 °C		1,1	1,3	V
		T _j = 150 °C		1	1,2	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		93,8		mΩ
		T _j = 150°C		156		$m\Omega$
V _{CE(sat)}	I _{Cnom} = 8 A, V _{GE} = 15 V			1,85	2,05	V
		$T_j = 150^{\circ}C_{chiplev.}$		2,25	2,45	V
C _{ies}				0,49		nF
C _{oes}	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,05		nF
C _{res}				0,03		nF
Q_G	V _{GE} =-7V+15V			37,5		nC
t _{d(on)}				16		ns
t _r	$R_{Gon} = 32 \Omega$	V _{CC} = 600V		14		ns
E _{on}	di/dt = 1375 A/µs	I _C = 8A		0,41 273		mJ
${f t}_{\sf d(off)} \ {f t}_{\sf f}$	$R_{Goff} = 32 \Omega$ di/dt = 1375 A/µs	T _j = 150 °C V _{GE} = ±15 V		273 85		ns ns
E _{off}		GE TIO		0,76		mJ
R _{th(j-s)}	per IGBT	•		2,2		K/W





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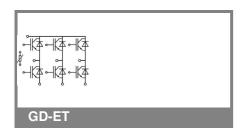
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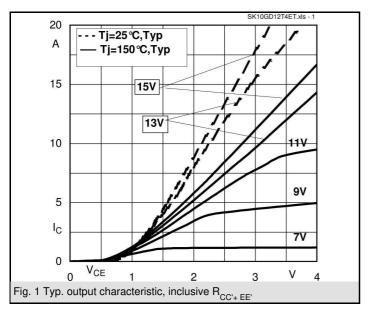
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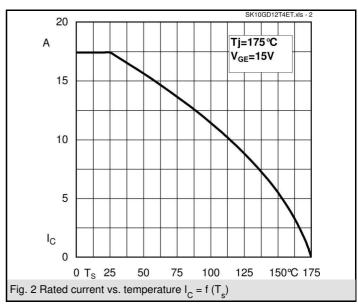
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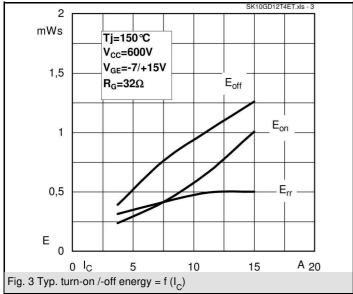
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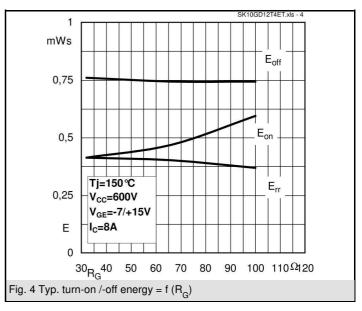
Characteristics							
Symbol	Conditions		min.	typ.	max.	Units	
Inverse D	iode					•	
$V_F = V_{EC}$	I_{Fnom} = 8 A; V_{GE} = 0 V	$T_j = 25 ^{\circ}C_{\text{chiplev.}}$		2,38	2,71	V	
		$T_j = 150 ^{\circ}C_{chiplev.}$		2,44	2,77	V	
V_{F0}		T _j = 25 °C		1,3	1,5	V	
		T _j = 150 °C		0,9	1,1	V	
r _F		T _j = 25 °C		135	151,3	mΩ	
		T _j = 150 °C		192	208,8	mΩ	
I _{RRM}	I _F = 8 A	T _j = 150 °C		15		Α	
Q_{rr}	di/dt = 1375 A/µs			0,2		μC	
E _{rr}	V _{CC} = 600V			0,41		mJ	
$R_{th(j-s)D}$	per diode			2,7		K/W	
M _s	to heat sink		2,25		2,5	Nm	
w				30		g	
Temperature sensor							
R ₁₀₀	$T_s = 100^{\circ}C (R_{25} = 5k\Omega)$			493±5%		Ω	

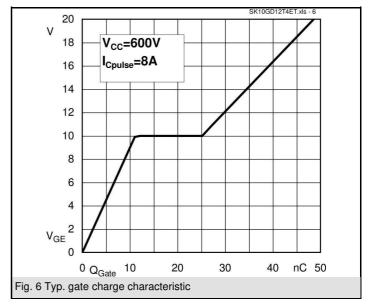


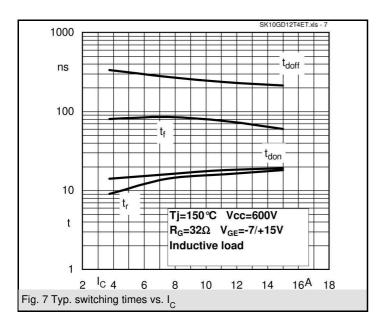


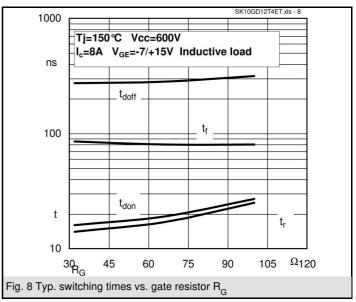


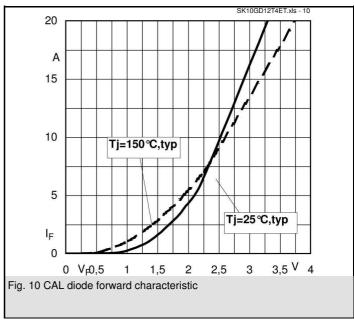




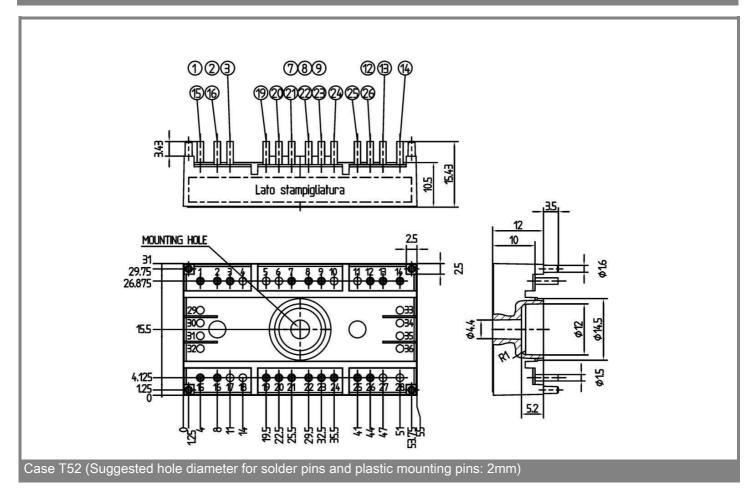


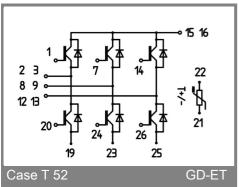






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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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